



STPS3060CW

POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

I _{F(AV)}	2 x 15 A
V _{RRM}	60 V
V _F (max)	0.65 V

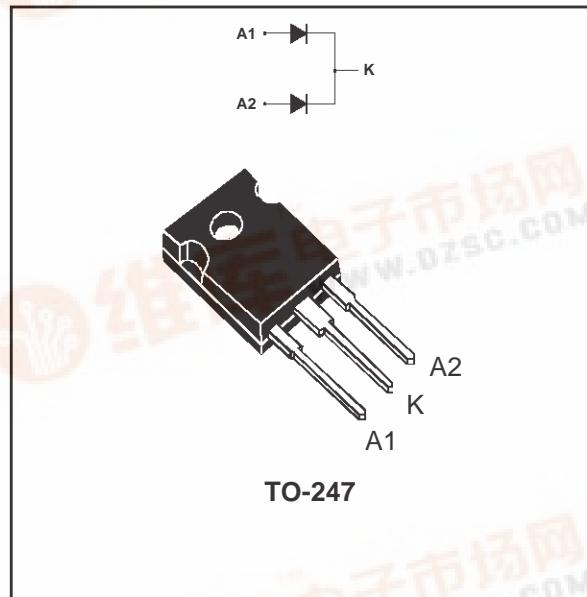
FEATURES AND BENEFITS

- HIGH REVERSE VOLTAGE
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE

DESCRIPTION

Dual center tap schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in TO-247 this device is intended for use in high frequency inverters.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		60	V
I _{F(RMS)}	RMS forward current		30	A
I _{F(AV)}	Average forward current	T _c = 125°C δ = 0.5	15	A
			30	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal	200	A
I _{RRM}	Peak repetitive reverse current	t _p = 2 μs F = 1kHz	1	A
T _{stg}	Storage temperature range		- 65 to + 150	°C
T _j	Maximum junction temperature		150	
dV/dt	Critical rate of rise reverse voltage		10000	V/μs

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6
		total	0.9
$R_{th(c)}$	Coupling	0.15	°C/W

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_J(\text{diode 1}) = P(\text{diode 1}) \times R_{th}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS PER DIODE

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_J = 25^\circ\text{C}$	$V_R = V_{RRM}$			30	μA
		$T_J = 125^\circ\text{C}$			5	25	mA
V_F **	Forward voltage drop	$T_J = 25^\circ\text{C}$	$I_F = 20 \text{ A}$			0.96	V
		$T_J = 125^\circ\text{C}$	$I_F = 20 \text{ A}$			0.8	
		$T_J = 125^\circ\text{C}$	$I_F = 10 \text{ A}$		0.58	0.65	

Pulse test : * $t_p = 5 \text{ ms}, \delta < 2\%$

** $t_p = 380 \mu\text{s}, \delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.56 \times I_{F(AV)} + 0.0113 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

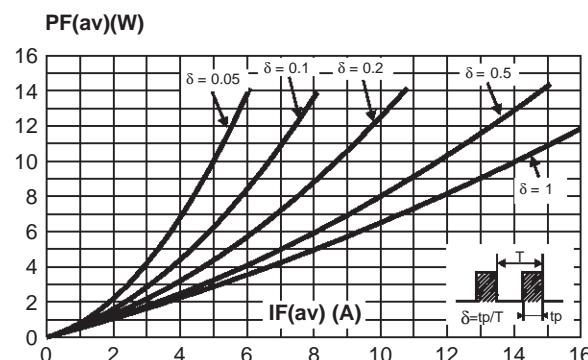


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$) (per diode).

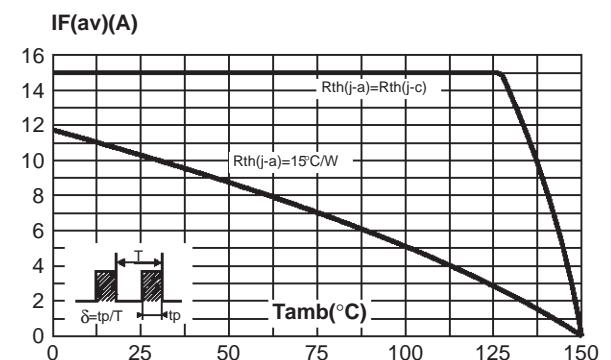


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

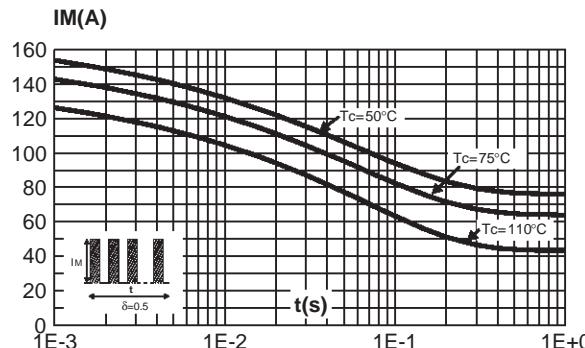


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

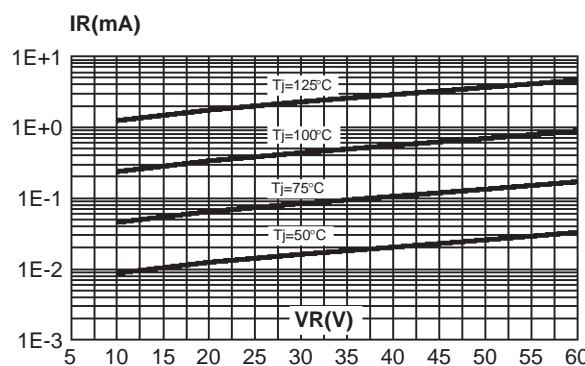


Fig. 7: Forward voltage drop versus forward current (maximum values) (per diode).

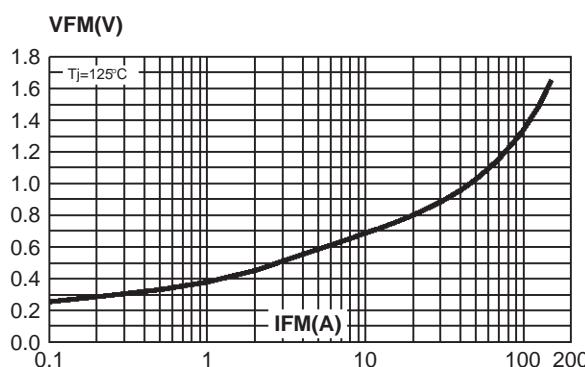


Fig. 4: Relative variation of thermal transient impedance junction to case versus pulse duration (per diode).

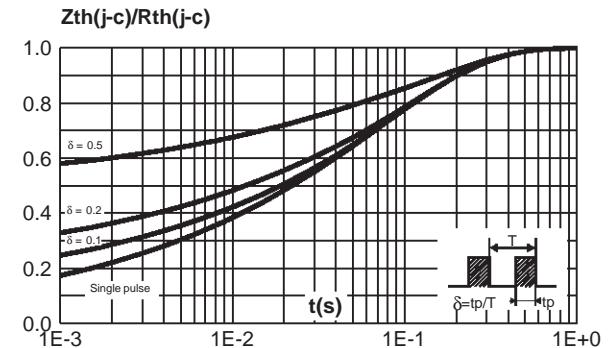
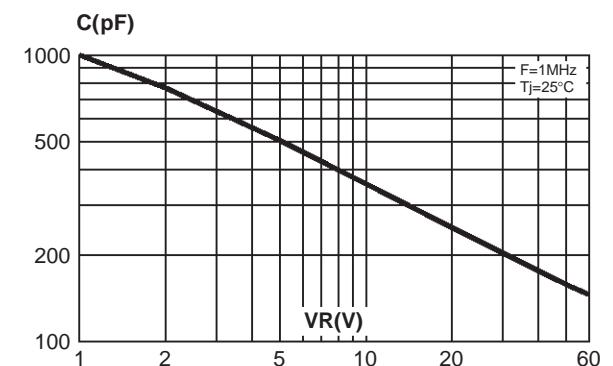


Fig. 6: Junction capacitance versus reverse voltage applied (typical values) (per diode).



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PACKAGE MECHANICAL DATA TO247

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

■ **Marking:** STPS3060CW

Cooling method : C

Weight: 4.4 g

Recommended torque value : 0.8m.N

Maximum torque value : 1.0m.N

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